

Type	L #	Hits	Search Text	DBs
1 BRS	L1	120067 9	sio? or "sio.sub.2" or oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2 BRS	L2	114515 8	oxidizing or oxidation or grow\$4 or thicken\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3 BRS	L3	6349	plasma near12 bias\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4 BRS	L4	607085	nitrogen or "n.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5 BRS	L5	121646	(nitrog\$4 near2 (oxygen or oxide)) or (no near2 gas\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6 BRS	L6	152617	(nitrog\$4 near2 (oxygen or oxide)) or (degree or deg?) near2 ("100" or "150" or "200" or "250")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7 BRS	L7	162096	(degree or deg?) near2 ("100" or "150" or "200" or "250")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	L #	Hits	Search Text	DBs
8	BRS	L8	0	3 same 2 same 6 same 7
9	BRS	L9	310108	plasma
10	BRS	L10	10	9 same 2 same 6 same 7
11	BRS	L11	311126	plasma or pecvd or pcvd
12	BRS	L12	30	11 same 6 same 7
13	BRS	L13	20	12 not 10
14	BRS	L14	18	13 and (@ay < "2000")

Type	L #	Hits	Search Text	DBs
15	BRS	L15	(complementary adj (metal adj (insulator or oxide) adj semiconductor adj (fet or field)) or cmos or cmis) and (thicken\$4 near8 (oxide or gate near2 (insulat\$4 or dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	(implant or implant or implanting or implanting) same (resist or photoresist or pr)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	11 same gate near3 (insulator or 1 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	(complementary adj (metal adj (insulator or oxide) adj semiconductor adj (fet or field)) or cmos or cmis)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	8 18 same 17 same 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	421 18 and 17 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	L21	336 20 and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	L #	Hits	Search Text	DBs
22	BRS	L22	982 11 near6 gate near3 (insulator or 1 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	L23	62 18 and 22 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	L24	49 23 and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	L25	15577 plasma adj enhanc\$4 or pecvd or pcvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	L26	138 25 near6 gate near3 (insulator or 1 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	BRS	L27	4 18 and 26 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	IS&R	L28	834 ((438/154) or (438/788) or (438/791)).CCLS.	USPAT; US-PGPUB